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EFFICIENT MULTI-PHYSICS MODELING OF THE DYNAMIC RESPONSE OF RF-MEMS SWITCHES

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- Intro RF-MEMS at EPCOS Netherlands
- Physics of capacitive MEMS switch
- FE model:

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- Coupling of physics domains
- Obtaining the static solution
- Homogenization of surface roughness
- Non-linear Reynolds for fluid / large signal transient
- Transient results & calibration with measurement
- Conclusion & outlook

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History of RF-MEMS and tuneable RF systems



Adaptive multi-band antenna optimized performance

- A plug and play antenna module
 - frequency band configurable
 - automatic performance optimization
- increased average RF output power
- increased battery time
- lower VSWR, more system margin



Measurement data LB: • uncorrected hand effects • hand effects corrected by AdAM





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Multiphysics modeling required

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Introduction RF-MEMS: Application example

Hand detuning effects effectively corrected – AdAM



Adaptation ON



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RF-MEMS capacitive switch

- Plate suspended by beams above bottom electrode covered with dielectric
- When a DC voltage is is supplied the plate is pulled-down thus creating a 20x larger capacitance between the electrodes





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Finite element model: key to predictive design

Capacitive switch is multi-physics problem:

- Bi-directional coupling between three different physics domains
- Non-linearities cause pull-in instability and convergence problems



Directly coupled fluid-electro-mechanical model

Fluid-mechanical coupling with iso-thermal non-linear compressible Reynolds equation in directly coupled element:



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Directly coupled electro-mechanical model

- Electro-mechanical coupling very efficient with transducer elements (only one mechanical DOF & 1 Volt DOF per node)
- C(z) of transducers from prior electrostatic simulation



Electrostatic model

- Dummy mesh used to map charge from electrostatic mesh to nearest mechanical node allows for dissimilar meshes
- Electrostatic simulation repeated for various (uniform) gap heights





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Solving Pull-in instability: DIPIE+

Displacement iterations scheme (DIPIE) can solve pull-in instability because for every displacement there is only one voltage solution

Fm + Fes = k·(z - gap0) +
$$\frac{\varepsilon 0 \cdot \text{Area} \cdot \text{V}^2}{2 \cdot z^2} = 0$$



Solving Pull-in instability: DIPIE+

Finite Element implementation DIPIE+ to find static CV-curve:

Consider <u>every</u> node to prescribe UZ displacement

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- Search for voltage for which reaction force vanishes
- Node selection based on largest electrostatic pressure increment

Even better: Numerical continuation



Multi-physics model: Validation of static solution

- Good agreement between measured and predicted CV curves
- Slope in closed state capacitance is important feature, caused by surface roughness of the contact





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Non-linear Contact model

measured from CV curve

-FEM simulation with AFM profile-1

1.8

Surface roughness is homogenized in non-linear contact model:

- Contact behavior pressure(displacement) can be extracted from CV curve
- Simulation of contact pressure-displacement using imported AFM profiles
- Exponential function (I.e. Greenwood model)
- Multi-linear approximation in gasket element

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Squeeze film theory

Implementation of new squeeze film element in Ansys:

- structural DOF's added to squeeze film element to create a directly coupled fluidstructural element
- Isothermal **non-linear compressible Reynolds equation** (because of large pressure changes when closing):

$$\frac{H}{p}\frac{\partial}{\partial t}p + \frac{\partial}{\partial t}H = \frac{H^{3}}{p12\mu} \left(\left(\frac{\partial}{\partial x}p\right)^{2} + \left(\frac{\partial}{\partial y}p\right)^{2} \right) + \frac{H^{3}}{12\mu}\nabla^{2}p$$

- Rarefied gas effects taken into account by an effective viscosity (with optional accommodation factors) as proposed by Veijola:
 - Diffuse reflection:

$$\mu_{eff} = \frac{\mu}{1 + 9.638 \cdot \left(\frac{L0 \cdot P_{L0}}{p \cdot H}\right)^{1.159}}$$

$$Kn = \frac{L0 \cdot P_{L0}}{p \cdot H}$$

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H=gap height (=Gap0-UZ) structural DOF

p=Pressure (DOF)

L0=molecular mean free path at P_{L0}

µ=viscosity

Kn= Knudsen number



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Effective viscosity extracted from measurements

- Impedance analyzer or LCR meter used to measure Re[Y]
- Parasitic shunt branch de-embedded before fitting mechanical Q-factor
- In vacuum chamber to vary ambient pressure

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Effective viscosity extracted from measurements

- Measure Q-factor for various designs, bias voltage & pressure range
- Simulate Q-factor's dependency on viscosity & bias voltage
 - Q-factor insensitive to exact match of first eigenfrequency



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Effective viscosity from measurements

Small deviation from Veijola

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Better fit obtained by introduction of accommodation factors



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Close/opening transient results

- 8x8 40V open & close transient at 0.4bar & 1bar cavity pressure
- FE model includes initial stress derived from interferometer profiles



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Linearized versus general Reynolds equation

- Significant difference between linearized & non-linear Reynolds
- Pressures clearly outside range for which linearization is valid



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- Demonstrated an efficient finite element implementation & validation of squeeze film effects for prediction of transient response
- Rarefaction effects were quantified by extracting the effective viscosity from measurements
- Transient simulations show good agreement with measurements of closing and opening cycles
- Multiphysics simulation improves the design by reducing the opening and closing times for the capacitive switch
- Non-linear Reynolds equation must be used for this type of devices





2020? This is what we'd like to have tomorrow:

- Advanced non-linear multi-physics solver to handle snap-backs:
 - Numerical-continuation e.g. Arc-length for multi-physics
- Non-linear materials in transient with acceptable run-times
 - Multi-size, multi-time scale solution
- More multi-physics domains for reliability assessments:
 - Charge diffusion for dielectric charging (specific for this MEMS)
 - HF-Electro Magnetic to predict power dissipation & temperature
 - Strain gradient crystal plasticity model (adds 18 DOF's) to handle size effects in materials (general for MEMS & NEMS)
- Integration of FE results in system/circuit simulation:
 - Predict large signal system performance (e.g. ACPR) with e.g. harmonic balance



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